

PNP SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

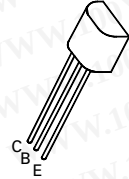
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FEATURES

- * 3.5 Amps continuous current
- * Up to 10 Amps peak current
- * Very low saturation voltage
- * Excellent gain up to 10 Amps
- * Spice model available

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

ZTX953



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-6	V
Peak Pulse Current	I_{CM}	-10	A
Continuous Collector Current	I_C	-3.5	A
Practical Power Dissipation*	P_{totp}	1.58	W
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1.2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-140	-170		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CE}$	-140	-170		V	$I_C = -1\mu A, R_B \leq 1K\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100	-120		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-8		V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}			-50 -1	nA μA	$V_{CB} = -100V$ $V_{CB} = -100V, T_{amb} = 100^{\circ}C$
Collector Cut-Off Current	I_{CER} $R \leq 1K\Omega$			-50 -1	nA μA	$V_{CB} = -100V$ $V_{CB} = -100V, T_{amb} = 100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-20 -80 -140 -250	-50 -100 -170 -330	mV mV mV mV	$I_C = 100mA, I_B = -10mA^*$ $I_C = 1A, I_B = -100mA^*$ $I_C = 2A, I_B = -200mA^*$ $I_C = 4A, I_B = -400mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-960	-1100	mV	$I_C = 4A, I_B = -400mA^*$

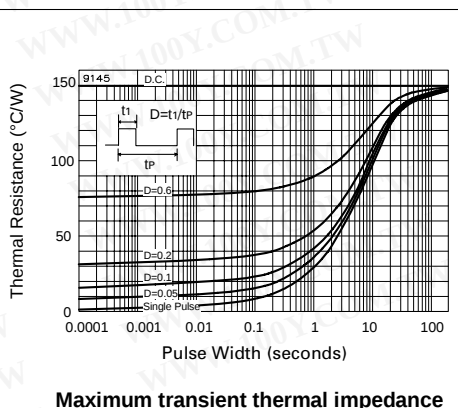
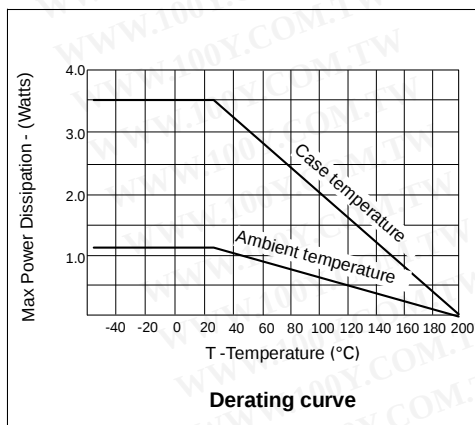
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-880	-1100	mV	$I_C = -4\text{A}$, $V_{CE} = -1\text{V}^*$
Static Forward Current Transfer	h_{FE}	100 100 50 30	200 200 90 50 15	300		$I_C = -10\text{mA}$, $V_{CE} = -1\text{V}^*$ $I_C = -1\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -3\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -4\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -10\text{A}$, $V_{CE} = -1\text{V}^*$
Transition Frequency	f_T		125		MHz	$I_C = -100\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{obo}		65		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		110 460		ns ns	$I_C = -2\text{A}$, $I_{B1} = -200\text{mA}$ $I_{B2} = 200\text{mA}$, $V_{CC} = -10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

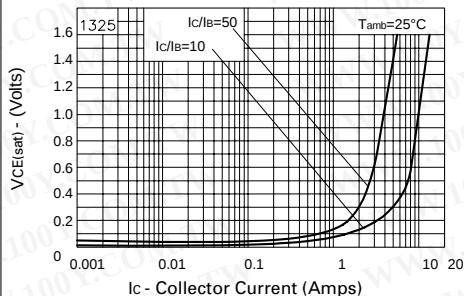
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient Junction to Case	$R_{th(j-amb)}$ $R_{th(j-case)}$	150 50	$^{\circ}\text{C/W}$ $^{\circ}\text{C/W}$



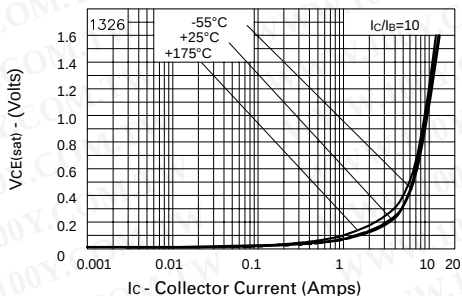
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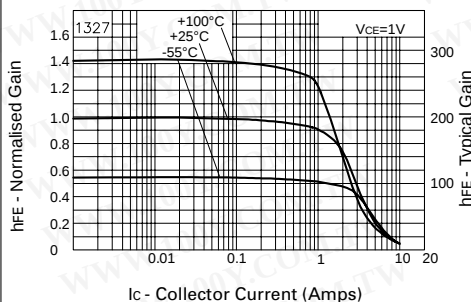
TYPICAL CHARACTERISTICS



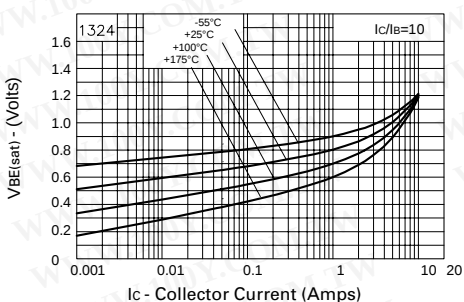
$V_{CE(sat)}$ v I_C



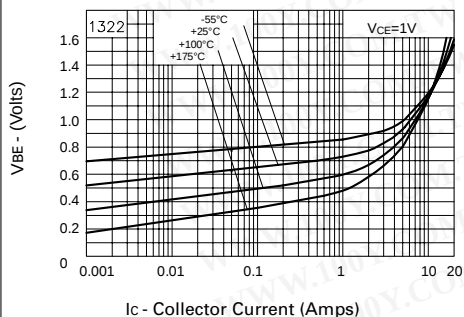
$V_{CE(sat)}$ v I_C



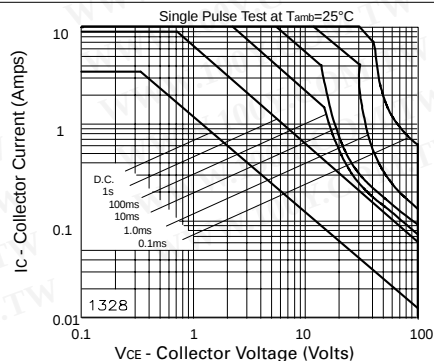
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area